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### Method for forming semiconductor device structure with a cap layer

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#### Abstract

A method for forming a semiconductor device structure includes forming nanostructures over a substrate. The method also includes forming a work function layer surrounding the nanostructures. The method also includes forming spacers over opposite sides of the work function layer. The method also includes forming a first metal layer over the work function layer and sidewalls of the spacers. The method also includes forming a second metal layer surrounded by the first metal layer. The method also includes etching the first metal layer over opposite sides of the second metal layer. The method also includes forming a cap layer over a top surface and a sidewall of the second metal layer.

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## Background/Summary

### BACKGROUND

(1) Semiconductor devices are used in a variety of electronic applications, such as personal computers, cell phones, digital cameras, and other electronic equipment. Semiconductor devices are typically fabricated by sequentially depositing insulating or ILD structures, conductive layers, and semiconductive layers of material over a semiconductor substrate, and patterning the various material layers using lithography to form circuit components and elements thereon. Many integrated circuits are typically manufactured on a single semiconductor wafer, and individual dies

on the wafer are singulated by sawing between the integrated circuits along a scribe line. The individual dies are typically packaged separately, in multi-chip modules, for example, or in other types of packaging.

(2) Recently, multi-gate devices have been introduced in an effort to improve gate control by increasing gate-channel coupling, reduce OFF-state current, and reduce short-channel effects (SCEs). One such multi-gate device that has been introduced is the gate-all around transistor (GAA). The GAA device gets its name from the gate structure which can extend around the channel region providing access to the channel on two or four sides. GAA devices are compatible with conventional complementary metal-oxide-semiconductor (CMOS) processes.

(3) However, integration of fabrication of the GAA features around the nanowire can be challenging. For example, while the current methods have been satisfactory in many respects, continued improvements are still needed.

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## Description

### BRIEF DESCRIPTION OF THE DRAWINGS

(1) Aspects of the present disclosure are best understood from the following detailed description when read with the accompanying figures. It should be noted that, in accordance with the standard practice in the industry, various features are not drawn to scale. In fact, the dimensions of the various features may be arbitrarily increased or reduced for clarity of discussion.

(2) FIG. 1 is a top view of a semiconductor device structure, in accordance with some embodiments of the disclosure.

(3) FIGS. 2A-2Y are perspective representations of various stages of forming a semiconductor device structure, in accordance with some embodiments of the disclosure.

(4) FIGS. 2P-1, 2Q-1, 2R-1, 2S-1, 2T-1, 2U-1, 2V-1, 2W-1, 2X-1, 2Y-1 are cross-sectional representations of various stages of forming a semiconductor device structure, in accordance with some embodiments of the disclosure.

(5) FIGS. 2S-2, 2T-2, 2U-2, 2V-2, 2W-2, 2X-2, 2Y-2 are cross-sectional representations of various stages of forming a semiconductor device structure, in accordance with some embodiments of the disclosure.

(6) FIGS. 3A-3E are perspective representations of various stages of forming a semiconductor device structure, in accordance with some embodiments of the disclosure.

(7) FIGS. 4A-4B are perspective representations of various stages of forming a semiconductor device structure, in accordance with some embodiments of the disclosure.

(8) FIGS. 5A-5D are perspective representations of various stages of forming a semiconductor device structure, in accordance with some embodiments of the disclosure.

(9) FIGS. 6A-6C are perspective representations of various stages of forming a semiconductor device structure, in accordance with some embodiments of the disclosure.

### DETAILED DESCRIPTION

(10) The following disclosure provides many different embodiments, or examples, for implementing different features of the subject matter provided. Specific examples of components and arrangements are described below to simplify the present disclosure. These are, of course, merely examples and are not intended to be limiting. For example, the formation of a first feature over or on a second feature in the description that follows may include embodiments in which the first and second features are formed in direct contact, and may also include embodiments in which additional features may be formed between the first and second features, such that the first and second features may not be in direct contact. In addition, the present disclosure may repeat reference numerals and/or letters in the various examples. This repetition is for the purpose of simplicity and clarity and does not in itself dictate a relationship between the various embodiments

and/or configurations discussed.

(11) Some variations of the embodiments are described. Throughout the various views and illustrative embodiments, like reference numbers are used to designate like elements. It should be understood that additional operations can be provided before, during, and after the method, and some of the operations described can be replaced or eliminated for other embodiments of the method.

(12) The gate all around (GAA) transistor structures described below may be patterned by any suitable method. For example, the structures may be patterned using one or more photolithography processes, including double-patterning or multi-patterning processes. Generally, double-patterning or multi-patterning processes combine photolithography and self-aligned processes, allowing patterns to be created that have, for example, smaller pitches than what is otherwise obtainable using a single, direct photolithography process. For example, in one embodiment, a sacrificial layer is formed over a substrate and patterned using a photolithography process. Spacers are formed alongside the patterned sacrificial layer using a self-aligned process. The sacrificial layer is then removed, and the remaining spacers may then be used to pattern the GAA structure.

(13) Embodiments for forming a semiconductor device structure are provided. The method for forming the semiconductor device structure may include forming an inverted T-shape gate structure by depositing different metal layers with different etching selectivity as the gate electrode. The cap layer may be formed between the gate electrode and the spacer layers. The parasitic capacitance may be reduced and device performance may be enhanced.

(14) FIG. 1 is a top view of a semiconductor structure **10a** in accordance with some embodiments. FIG. 1 has been simplified for the sake of clarity to better understand the inventive concepts of the present disclosure. Additional features may be added in the semiconductor structure **10a**, and some of the features described below may be replaced, modified, or eliminated.

(15) The semiconductor structure **10a** may include multi-gate devices and may be included in a microprocessor, a memory, or other IC devices. For example, the semiconductor structure **10a** may be a portion of an IC chip that include various passive and active microelectronic devices such as resistors, capacitors, inductors, diodes, p-type field effect transistors (PFETs), n-type field effect transistors (NFETs), metal-oxide semiconductor field effect transistors (MOSFETs), complementary metal-oxide semiconductor (CMOS) transistors, bipolar junction transistors (BJTs), laterally diffused MOS (LD MOS) transistors, high voltage transistors, high frequency transistors, other applicable component, or a combination thereof.

(16) FIGS. 2A-2Y are perspective representations of various stages of forming a semiconductor device structure **10a**, in accordance with some embodiments of the disclosure. More specifically, FIGS. 2A-2Q illustrate perspective views of intermediate stages of manufacturing the semiconductor structure **10a** shown in the dotted line block C1 of FIG. 1, and FIGS. 2R to 2Y illustrate diagrammatic perspective views of intermediate stages of manufacturing the semiconductor structure **10a** shown in the dotted line block C2 of FIG. 1 in accordance with some embodiments.

(17) The semiconductor device structure **10a** may be a gate all around (GAA) transistor structure. FIGS. 2P-1, 2Q-1, 2R-1, 2S-1, 2S-2, 2T-1, 2T-2, 2U-1, 2U-2, 2V-1, 2V-2, 2W-1, 2W-2, 2X-1, 2X-2, 2Y-1, 2Y-2 are cross-sectional representations of various stages of forming a semiconductor device structure **10a**, in accordance with some embodiments of the disclosure. FIGS. 2P-1, 2Q-1, 2R-1, 2S-1, 2T-1, 2U-1, 2V-1, 2W-1, 2X-1, 2Y-1 show cross-sectional representations taken along line 1-1 in FIGS. 2P, 2Q, 2R, 2S, 2T, 2U, 2V, 2W, 2X, 2Y, respectively. FIGS. 2S-2, 2T-2, 2U-2, 2V-2, 2W-2, 2X-2, 2Y-2 show cross-sectional representations taken along line 2-2 in FIGS. 2S, 2T, 2U, 2V, 2W, 2X, 2Y, respectively.

(18) A semiconductor stack including first semiconductor material layers **106** and second semiconductor material layers **108** are formed over a substrate **102**, as shown in FIG. 2A in accordance with some embodiments. The substrate **102** may be a semiconductor wafer such as a

silicon wafer. The substrate **102** may also include other elementary semiconductor materials, compound semiconductor materials, and/or alloy semiconductor materials. Examples of the elementary semiconductor materials may include, but are not limited to, crystal silicon, polycrystalline silicon, amorphous silicon, germanium, and/or diamond. Examples of the compound semiconductor materials may include, but are not limited to, silicon carbide, gallium nitride, gallium arsenic, gallium phosphide, indium phosphide, indium arsenide, and/or indium antimonide. Examples of the alloy semiconductor materials may include, but are not limited to, SiGe, GaAsP, AlInAs, AlGaAs, GaInAs, GaInP, and/or GaInAsP. The substrate **102** may include an epitaxial layer. For example, the substrate **102** may be an epitaxial layer overlying a bulk semiconductor. In addition, the substrate **102** may also be semiconductor on insulator (SOI). The SOI substrate may be fabricated by a wafer bonding process, a silicon film transfer process, a separation by implantation of oxygen (SIMOX) process, other applicable methods, or a combination thereof. The substrate **102** may be an N-type substrate. The substrate **102** may be a P-type substrate.

(19) Next, first semiconductor material layers **106** and second semiconductor material layers **108** are alternating stacked over the substrate **102** to form the semiconductor stack, as shown in FIG. 2A in accordance with some embodiments. The first semiconductor material layers **106** and the second semiconductor material layers **108** may include Si, Ge, SiGe, GaAs, InSb, GaP, GaSb, InAlAs, InGaAs, GaSbP, GaAsSb, or InP. The first semiconductor material layers **106** and second semiconductor material layers **108** may be made of different materials with different etching rates. In some embodiments, for example, the first semiconductor material layers **106** are made of SiGe and the second semiconductor material layers **108** are made of Si.

(20) The first semiconductor material layers **106** and second semiconductor material layers **108** may be formed by low pressure chemical vapor deposition (LPCVD) process, epitaxial growth process, other applicable methods, or a combination thereof. The epitaxial growth process may include molecular beam epitaxy (MBE), metal organic chemical vapor deposition (MOCVD), or vapor phase epitaxy (VPE).

(21) It should be noted that, although there are three layers of the first semiconductor material layers **106** and three layers of the second semiconductor material layers **108** shown in FIG. 2A, the number of the first semiconductor material layers **106** and second semiconductor material layers **108** are not limited herein, depending on the demand of performance and process. For example, the semiconductor structure may include two to five layers of the first semiconductor material layers **106** and two to five layers of the second semiconductor material layers **108**.

(22) After the first semiconductor material layers **106** and the second semiconductor material layers **108** are formed as the semiconductor material stack over the substrate **102**, the semiconductor material stack is patterned to form fin structures **104** using the patterned mask structure **110** as a mask layer, as shown in FIG. 2B in accordance with some embodiments. In some embodiments, the fin structures **104** include base fin structures **105** and the semiconductor material stacks, including the first semiconductor material layers **106** and the second semiconductor material layers **108**, formed over the base fin structure **105**.

(23) The patterning process may including forming a mask structure **110** over the first semiconductor material layers **106** and the second semiconductor material layers **108** and etching the semiconductor material stack and the underlying substrate **102** through the mask structure **110**, as shown in FIG. 2B in accordance with some embodiments. The mask structure **110** may be a multilayer structure including a pad layer **112** and a hard mask layer **114** formed over the pad layer **112**. The pad layer **112** may be made of silicon oxide, which may be formed by thermal oxidation or CVD. The hard mask layer **114** may be made of silicon nitride, which may be formed by CVD, such as LPCVD or plasma-enhanced CVD (PECVD).

(24) The patterning process of forming the fin structures **104** may include a photolithography process and an etching process. The photolithography process may include photoresist coating

(e.g., spin-on coating), soft baking, mask aligning, exposure, post-exposure baking, developing the photoresist, rinsing and drying (e.g., hard baking). The etching process may include a dry etching process or a wet etching process.

(25) After the fin structures **104** are formed, a liner layer **117** is formed over the fin structures **104** and in the trenches between the fin structures **104**, as shown in FIG. 2C in accordance with some embodiments. The liner layer **117** may be conformally formed over the substrate **102**, the fin structure **104**, and the mask structure **110** covering the fin structure **104**. The liner layer **117** may be used to protect the fin structure **104** from being damaged in the following processes (such as an anneal process or an etching process). The liner layer **117** may be made of silicon nitride. The liner layer **117** may be formed by using a thermal oxidation, a CVD process, an atomic layer deposition (ALD) process, a LPCVD process, a plasma enhanced CVD (PECVD) process, a HDPCVD process, a flowable CVD (FCVD) process, another applicable process, or a combination thereof.

(26) Next, an isolation structure material **119** is then filled over the liner layer **117** in the trenches between the fin structures **104**, as shown in FIG. 2D in accordance with some embodiments. The isolation structure material **119** may be made of silicon oxide, silicon nitride, silicon oxynitride (SiON), fluoride-doped silicate glass (FSG), other low-k dielectric materials, or a combination thereof. The isolation structure material **119** may be deposited by a deposition process, such as a chemical vapor deposition (CVD) process (e.g. a flowable CVD (FCVD) process), a spin-on-glass process, or another applicable process.

(27) Next, the isolation structure material **119** and the liner layer **117** are etched back by an etching process, and an isolation structure **116** is formed surrounding the base fin structure **105**, as shown in FIG. 2E in accordance with some embodiments. The etching process may be used to remove the top portion of the liner layer **117** and the top portion of the isolation structure material **119**. As a result, the first semiconductor material layers **106** and the second semiconductor material layers **108** may be exposed. The isolation structure **116** may be a shallow trench isolation (STI) structure. The isolation structure **116** may be configured to electrically isolate active regions such as fin structures **104** of the semiconductor structure **10a** and prevent electrical interference or crosstalk.

(28) Next, a semiconductor liner layer (not shown) may be formed over the fin structures **104**. The semiconductor liner may be a Si layer and may be incorporated into the subsequently formed cladding layer during the epitaxial growth process for forming the cladding layer.

(29) After the semiconductor liner layer is formed, a cladding layer **118** is formed over the top surfaces and the sidewalls of the fin structures **104** and over the isolation structure **116**, as shown in FIG. 2F in accordance with some embodiments. The cladding layer **118** may be made of semiconductor materials such as silicon germanium (SiGe). The cladding layer **118** and the first semiconductor material layers **106** may be made of the same material.

(30) The cladding layer **118** may be formed by performing an epitaxy process, such as VPE and/or UHV CVD, molecular beam epitaxy, other applicable epitaxial growth processes, or a combination thereof. After the cladding layer **118** is deposited, an etching process may be performed to remove the portion of the cladding layer **118** not formed on the sidewalls of the fin structures **104**. The cladding layer **118** formed over the top surface of the isolation structure **116** is partially or completely removed by the etching process, such that the thickness of the cladding layer **118** over the top surface of the fin structures **104** is thinner than the thickness of the cladding layer **118** on the sidewalls of the fin structures **104**. The etching process may include a plasma dry etching process.

(31) Next, a dielectric liner **120** is formed over the cladding layers **118** and the isolation structure **116**, as shown in FIG. 2G in accordance with some embodiments. The dielectric liner **120** may be made of a low k dielectric material having a k value lower than 7. The dielectric liner **120** may be made of oxide, nitride, SiN, SiCN, SiOCN, SiON, or the like. The dielectric liner **120** may be deposited using CVD, PVD, ALD, HDPCVD, MOCVD, RPCVD, PECVD, LPCVD, ALCVD, APCVD, other applicable methods, or a combination thereof.

(32) Next, a fin isolation material **122** is formed to completely fill the spaces between the adjacent fin structures **104**, and a planarization process is performed until the top surfaces of the cladding layers **118** are exposed, as shown in FIG. 2H in accordance with some embodiments. The fin isolation material **122** may be made of a low k dielectric material such as oxide, nitride, SiN, SiCN, SiOCN, SiON, or the like. The fin isolation material **122** and the dielectric liner **120** may be made of different dielectric materials. The fin isolation material **122** and the dielectric liner **120** may both be made of oxide formed by different methods. The fin isolation material **122** may be deposited using a flowable CVD (FCVD) process that includes, for example, depositing a flowable material (such as a liquid compound) and converting the flowable material to a solid material by a suitable technique, such as thermal annealing and/or ultraviolet radiation treating. The planarizing process may include a grinding process, a chemical mechanical polishing (CMP) process, an etching process, other applicable processes, or a combination thereof.

(33) Next, the top portion of the fin isolation material **122** and the dielectric liner **120** are recessed to form a fin isolation structure **122**, and a dielectric material **126** is formed in the recesses to form the dielectric structure **134** separating the fin structures **104**, as shown in FIG. 2I in accordance with some embodiments. In some embodiments, the dielectric structure **134** includes the fin isolation structure **122** and the dielectric material **126** formed over the fin isolation structure **122**. The fin isolation material **122** may be recessed by an etching process. The etching process may include a dry etching process or a wet etching process.

(34) The dielectric material **126** may be made of high-k dielectric material such as metal oxides, metal nitrides, metal silicates, transition metal-oxides, transition metal-nitrides, transition metal-silicates, oxynitrides of metals, other suitable materials, or a combination thereof. Examples of the high-k dielectric material include, but are not limited to, hafnium oxide (HfO<sub>2</sub>), hafnium silicon oxide (HfSiO), hafnium silicon oxynitride (HfSiON), hafnium tantalum oxide (HfTaO), hafnium titanium oxide (HfTiO), hafnium zirconium oxide (HfZrO), zirconium oxide, titanium oxide, aluminum oxide, hafnium dioxide-alumina (HfO<sub>2</sub>-Al<sub>2</sub>O<sub>3</sub>) alloy, or other applicable dielectric materials.

(35) In some embodiments, the dielectric constant of the dielectric material **126** is higher than that of the fin isolation structure **122**. The dielectric material **126** may be formed by performing ALD, CVD, PVD, oxidation-based deposition process, other suitable process, or a combination thereof. After the dielectric material **126** is formed, a planarization process may be performed until the mask structure **110** is exposed.

(36) In some embodiments, the interface between the dielectric material **126** and the fin isolation structure **122** is lower than the top surface of the topmost second semiconductor material layers **108** and higher than the bottom surface of the topmost second semiconductor material layers **108**.

(37) Next, the mask structure **110** including the pad layer **112** and the hard mask layer **114** is removed, and the upper portions of the cladding layer **118** are partially removed to expose the top surfaces of the topmost second semiconductor material layers **108**, as shown in FIG. 2J in accordance with some embodiments. More specifically, the upper portions of the cladding layer **118** are removed first, and the mask structure **110** is removed afterwards in accordance with some embodiments. The top surfaces of the cladding layers **118** are substantially level with the top surfaces of the topmost second semiconductor material layers **108**. The mask structures **107** and the cladding layers **118** may be recessed by performing an etching process. The etching processes may be dry etching, wet drying, reactive ion etching, or other applicable etching methods.

(38) Next, a dummy gate structure **128** is formed over and across the fin structures **104**, the cladding layer **118**, and the dielectric structure **134**, as shown in FIG. 2K in accordance with some embodiments. The dummy gate structures **128** may be used to define the source/drain regions and the channel regions of the resulting semiconductor structure **10a**. The dummy gate structure **128** may include a dummy gate dielectric layer **130** and a dummy gate electrode layer **132**. The dummy gate dielectric layer **130** and the dummy gate electrode layer **132** may be replaced by the following



steps to form a real gate structure with a high-k dielectric layer and a metal gate electrode layer.

(39) The dummy gate dielectric layer **130** may include one or more dielectric materials, such as silicon oxide, silicon nitride, silicon oxynitride (SiON), HfO<sub>2</sub>, HfZrO, HfSiO, HfTiO, HfAlO, or a combination thereof. The dummy gate dielectric layer **130** may be formed by an oxidation process (e.g., a dry oxidation process, or a wet oxidation process), a chemical vapor deposition process, other applicable processes, or a combination thereof. Alternatively, the dummy gate dielectric layer **130** may include a high-k dielectric layer (e.g., the dielectric constant is greater than 3.9) such as hafnium oxide (HfO<sub>2</sub>). Alternatively, the high-k dielectric layer may include other high-k dielectrics, such as LaO, AlO, ZrO, TiO, Ta<sub>2</sub>O<sub>5</sub>, Y<sub>2</sub>O<sub>3</sub>, SrTiO<sub>3</sub>, BaTiO<sub>3</sub>, BaZrO, HfZrO, HfLaO, HfTaO, HfSiO, HfSiON, HfTiO, LaSiO, AlSiO, (Ba, Sr)TiO<sub>3</sub>, Al<sub>2</sub>O<sub>3</sub>, other applicable high-k dielectric materials, or a combination thereof. The high-k dielectric layer may be formed by a chemical vapor deposition process (e.g., a plasma enhanced chemical vapor deposition (PECVD) process, or a metalorganic chemical vapor deposition (MOCVD) process), an atomic layer deposition (ALD) process (e.g., a plasma enhanced atomic layer deposition (PEALD) process), a physical vapor deposition (PVD) process (e.g., a vacuum evaporation process, or a sputtering process), other applicable processes, or a combination thereof.

(40) The dummy gate electrode layer **132** may include polycrystalline-silicon (poly-Si), polycrystalline silicon-germanium (poly-SiGe), other applicable materials, or a combination thereof. The dummy gate electrode layer **132** may be formed by a chemical vapor deposition process (e.g., a low pressure chemical vapor deposition process, or a plasma enhanced chemical vapor deposition process), a physical vapor deposition process (e.g., a vacuum evaporation process, or a sputtering process), other applicable processes, or a combination thereof.

(41) Hard mask layers **136** are formed over the dummy gate structures **128**, as shown in FIG. 2K in accordance with some embodiments. The hard mask layers **136** may include multiple layers, such as an oxide layer **136a** and a nitride layer **136b**. In some embodiments, the oxide layer **136a** is silicon oxide, and the nitride layer **136b** is silicon nitride.

(42) The formation of the dummy gate structures **128** may include conformally forming a dielectric material as the dummy gate dielectric layers **130**. Afterwards, a conductive material may be formed over the dielectric material as the dummy gate electrode layers **132**, and the bi-layered hard mask layers **136**, including the oxide layer **136a** and the nitride layer **136b**, may be formed over the conductive material. Next, the dielectric material and the conductive material may be patterned and etched through the bi-layered hard mask layers **136** to form the dummy gate structures **128**, as shown in FIG. 2K in accordance with some embodiments. The dummy gate dielectric layer **130** and the dummy gate electrode layer **132** may be etched by a dry etching process. After the etching process, the first semiconductor material layers **106** and the second semiconductor material layers **108** may be exposed on opposite sides of the dummy gate structure **128**.

(43) Next, a conformal dielectric layer is formed over the substrate **102** and the dummy gate structure **128**, and then an etching process is performed. A pair of spacer layers **138** is formed over opposite sidewalls of the dummy gate structure **128**, and a source/drain opening is formed between adjacent dummy gate structures **128**, as shown in FIG. 2L in accordance with some embodiments.

(44) In some embodiments, the spacer layers **138** are multi-layer structures including the first spacer layers **138a** and the second spacer layers **138b**. In some embodiments, the first spacer layer **138a** is conformally formed over sidewalls of the dummy gate structure **128** and the dielectric material **126**, and the second spacer layers **138b** is formed over the first spacer layer **138a**. The first spacer layer **138** may have an L-shape in the cross-sectional view.

(45) The first spacer layers **138a** and the second spacer layers **138b** may be made of silicon oxide, silicon nitride, silicon oxynitride, and/or dielectric materials. The first spacer layers **138a** and second spacer layers **138b** may be formed by different materials with different etching selectivity. In some embodiments, the first spacer layers **138a** and the second spacer layers **138b** are made of

silicon nitride with different etching selectivity. The first spacer layers **138a** and second spacer layers **138b** may be formed by a chemical vapor deposition (CVD) process, a spin-on-glass process, or another applicable process.

(46) After the spacer layers **138** are formed, the first semiconductor material layers **106** and the second semiconductor material layers **108** of the fin structure **104** and the cladding layer **118** not covered by the dummy gate structures **128** and the spacer layers **138** are etched to form the trenches **140**, as shown in FIG. 2L in accordance with some embodiments.

(47) The fin structures **104** and the cladding layer **118** may be recessed by performing a number of etching processes. That is, the first semiconductor material layers **106** and the second semiconductor material layers **108** of the fin structures **104** and the cladding layer **118** may be etched in different etching processes. In addition, the dielectric material **126** not covered by the dummy gate structures **128** and the spacer layers **138** are also partially etched to form recessed portions **127** during the etching processes in accordance with some embodiments. That is, the dielectric material **126** is thicker under the dummy gate structure **128** and the spacer layers **138**, as shown in FIG. 2L in accordance with some embodiments.

(48) The etching process may be a dry etching process or a wet etching process. In some embodiments, the fin structures **104** and the cladding layer **118** are etched by a dry etching process.

(49) Next, the first semiconductor material layers **106** are laterally etched from the source/drain opening to form recesses (not shown). The outer portions of the first semiconductor material layers **106** may be removed, and the inner portions of the first semiconductor material layers **106** under the dummy gate structures **128** and the spacer layers **138** may remain. After the lateral etching process, the sidewalls of the etched first semiconductor material layers **106** may be not aligned with the sidewalls of the second semiconductor material layers **108**. The cladding layer **118** may be exposed in the recess.

(50) The lateral etching of the first semiconductor material layers **106** may be a dry etching process, a wet etching process, or a combination thereof. In some embodiments, the first semiconductor material layers **106** are Ge or SiGe and the second semiconductor material layers **108** are Si, and the first semiconductor material layers **106** are selectively etched to form the recesses by using a wet etchant such as, but not limited to, ammonium hydroxide (NH<sub>4</sub>OH), tetramethylammonium hydroxide (TMAH), ethylenediamine pyrocatechol (EDP), or potassium hydroxide (KOH) solutions, or the like.

(51) Next, an inner spacer **142** is formed in the recess, as shown in FIG. 2M in accordance with some embodiments. The inner spacer **142** may provide a barrier between subsequently formed source/drain epitaxial structures and gate structure. The inner spacer **142** may be made of dielectric material such as silicon oxide (SiO<sub>2</sub>), silicon nitride (SiN), silicon carbide (SiC), silicon oxynitride (SiON), silicon carbon nitride (SiCN), silicon oxide carbonitride (SiOCN), or a combination thereof. The inner spacer **142** may be formed by a deposition process. The deposition process may include a CVD process (such as LPCVD, PECVD, SACVD, or FCVD), an ALD process, another applicable method, or a combination thereof.

(52) Next, a source/drain epitaxial structure **144** is formed in the source/drain opening, as shown in FIG. 2N in accordance with some embodiments. The source/drain epitaxial structure **144** may be formed over opposite sides of the dummy gate structure **128**.

(53) A strained material may be grown in the source/drain opening by an epitaxial (epi) process to form the source/drain epitaxial structure **144**. In addition, the lattice constant of the strained material may be different from the lattice constant of the substrate **102**. The source/drain epitaxial structure **144** may include Ge, SiGe, InAs, InGaAs, InSb, GaAs, GaSb, InAlP, InP, SiC, SiP, other applicable materials, or a combination thereof. The source/drain epitaxial structure **144** may be formed by an epitaxial growth step, such as metalorganic chemical vapor deposition (MOCVD), metalorganic vapor phase epitaxy (MOVPE), plasma-enhanced chemical vapor deposition (PECVD), remote plasma-enhanced chemical vapor deposition (RP-CVD), molecular beam epitaxy

(MBE), hydride vapor phase epitaxy (HVPE), liquid phase epitaxy (LPE), chloride vapor phase epitaxy (Cl-VPE), or any other suitable method.

(54) In some embodiments, the source/drain epitaxial structures **144** are in-situ doped during the epitaxial growth process. For example, the source/drain epitaxial structures **144** may be the epitaxially grown SiGe doped with boron (B). For example, the source/drain epitaxial structures **144** may be the epitaxially grown Si doped with carbon to form silicon:carbon (Si:C) source/drain features, phosphorous to form silicon:phosphor (Si:P) source/drain features, or both carbon and phosphorous to form silicon carbon phosphor (SiCP) source/drain features. The source/drain epitaxial structures **144** may be doped in one or more implantation processes after the epitaxial growth process.

(55) Next, a contact etch stop layer **148** is formed over the source/drain epitaxial structure **144**, as shown in FIG. 20 in accordance with some embodiments. More specifically, the contact etch stop layers **148** cover the sidewalls of the spacer layers **138**, the top surfaces and sidewalls of the recessed portion **127** of the dielectric materials **126**, and the source/drain structures **144** in accordance with some embodiments.

(56) The contact etch stop layer **148** may be made of a dielectric material such as silicon nitride, silicon oxide, silicon oxynitride (SiON), other applicable materials, or a combination thereof. The contact etch stop layer **148** may be formed by a chemical vapor deposition process (e.g., a plasma enhanced chemical vapor deposition (PECVD) process, or a metalorganic chemical vapor deposition (MOCVD) process), an atomic layer deposition (ALD) process (e.g., a plasma enhanced atomic layer deposition (PEALD) process), a physical vapor deposition (PVD) process (e.g., a vacuum evaporation process, or a sputtering process), other applicable processes, or a combination thereof.

(57) After the contact etch stop layer **148** is formed, an inter-layer dielectric (ILD) structure **150** is formed over the contact etch stop layer **148**, as shown in FIG. 20 in accordance with some embodiments. The ILD structure **150** may include multilayers made of multiple dielectric materials, such as silicon oxide (SiO.sub.x, where x may be a positive integer), silicon oxycarbide (SiCO.sub.y, where y may be a positive integer), silicon oxycarbonitride (SiNCO.sub.z, where z may be a positive integer), silicon nitride, silicon oxynitride, phosphosilicate glass (PSG), borophosphosilicate glass (BPSG), low-k dielectric material, or other applicable dielectric materials. Examples of low-k dielectric materials include, but are not limited to, fluorinated silica glass (FSG), carbon doped silicon oxide, amorphous fluorinated carbon, parylene, bis-benzocyclobutenes (BCB), or polyimide. The ILD structure **150** may be formed by chemical vapor deposition (CVD), physical vapor deposition, (PVD), atomic layer deposition (ALD), spin-on coating, or other applicable processes.

(58) Afterwards, a planarizing process or an etch-back process is performed on the ILD structure **150** until the top surface of the dummy gate structure **128** is exposed, as shown in FIG. 20 in accordance with some embodiments. After the planarizing process, the top surface of the dummy gate structure **128** may be substantially level with the top surfaces of the spacer layers **138** and the ILD structure **150**. The planarizing process may include a grinding process, a chemical mechanical polishing (CMP) process, an etching process, other applicable processes, or a combination thereof.

(59) Afterwards, a protection layer **164** is formed over the interlayer dielectric layer **150**, as shown in FIG. 20 in accordance with some embodiments. More specifically, after the planarization process is performed, the ILD structure **150** is recessed and the protection layer **164** is deposited over the ILD structure **150** to protect the ILD structure **150** from subsequent etching processes. The protection layer **164** may be made of a material that is the same as or similar to that in the contact etch stop layer **130**. The protection layer **164** may be made of Si.sub.3N.sub.4, SiCN, SiOCN, SiOC, a metal oxide such as HfO.sub.2, ZrO.sub.2, hafnium aluminum oxide, and hafnium silicate, or other applicable material. The protection layer **164** may be formed by CVD, PVD, ALD, or other applicable methods.

(60) Next, the dummy gate structure **128** and the top portion of the spacer layers **138a** and **138b** are removed, as shown in FIGS. 2P and 2P-1 in accordance with some embodiments. Therefore, a trench **152** is formed between the spacer layers **138** over the fin structure **104** and the second semiconductor material layers **108** are exposed from the trench **152**.

(61) The bottom portion of the spacer layers **138** may remain after the removal of the dummy gate structure **128**. In some embodiments, the top surfaces of the bottom portion of the spacer layers **138** are exposed in the trench **152**. In some embodiments, the top surface of the spacer layers **138a** is substantially aligned with the top surface of the spacer layers **138b**. In some embodiments, the bottom of the trench **152** is narrower than the top of the top of the trench **152**.

(62) The dummy gate structure **128** and the top portion of the spacer layers **138** may be removed by a dry etching process or a wet etching process. The removal process may include one or more etching processes. For example, when the dummy gate electrode layers **132** are polysilicon, a wet etchant such as a tetramethylammonium hydroxide (TMAH) solution may be used to selectively remove the dummy gate electrode layers **132**. Afterwards, the dummy gate dielectric layers **130** may be removed using a plasma dry etching, a dry chemical etching, and/or a wet etching.

(63) After the dummy gate structures **128** are removed, the dielectric material **126** of the dielectric structure **134** exposed by the trenches **152** is patterned, as shown in FIGS. 2Q and 2Q-1 in accordance with some embodiments. The remaining portions **126a** of the dielectric material **126** may be configured to separate the gate structures formed afterwards into various portions and may therefore be left over the fin isolation structure **122**. In some embodiments, the top surface of the remaining portion **126b** of the dielectric material **126a** is substantially level with the top surface of the topmost second semiconductor material layer **108**.

(64) After the dielectric material **126** of the dielectric structure **134** is patterned, the first semiconductor material layers **106** and the cladding layer **118** are removed, as shown in FIGS. 2R and 2R-1 in accordance with some embodiments. More specifically, the second semiconductor material layers **108** exposed by the trenches **152** form nanostructures **108**, and the nanostructures **108** are configured to function as channel regions in the resulting semiconductor devices **10a** in accordance with some embodiments.

(65) The first semiconductor material layers **106** and the cladding layer **118** may be removed by performing one or more etching processes. For example, the cladding layer **118** may be etched to form gaps between the fin structure **104** and the fin isolation structure **122**, and the first semiconductor material layers **106** may be removed through the gaps afterwards. The cladding layer **118** may help to remove the first semiconductor material layers **106** and to form the nanostructures **108** more efficiently.

(66) The etching process may include a selective wet etching process, such as APM (e.g., ammonia hydroxide-hydrogen peroxide-water mixture) etching process. In some embodiments, the wet etching process uses etchants such as ammonium hydroxide (NH<sub>4</sub>OH), TMAH, ethylenediamine pyrocatechol (EDP), and/or potassium hydroxide (KOH) solutions.

(67) The isolation structure **116** and the liner layer **117** may be consumed in the etching process of removing the first semiconductor material layers **106** and the cladding layer **118**. In some embodiments, the top surfaces of the isolation structure **116** and the liner layer **117** are lower than the top surface of the base fin structure **105** after the etching process.

(68) Next, gate structures **168** are formed surrounding the nanostructures **108** and over the nanostructures **108**. Gate structures **168** are formed surrounding the nanostructure **108** to form gate-all-around (GAA) transistor structures, as shown in FIGS. 2S, 2S-1 and 2S-2 in accordance with some embodiments. Therefore, the gate control ability may be enhanced.

(69) In some embodiments as shown in FIGS. 2S, 2S-1 and 2S-2, the gate structures **168** are multi-layered structures. Each of the gate structures **168** may include an interfacial layer **170**, a gate dielectric layer **172**, a first work function layer **173a** and a second work function layer **173b**, a glue layer **174**, and a gate electrode layer, as shown in FIGS. 2S, 2S-1 and 2S-2 in accordance with

some embodiments.

(70) The interfacial layer **170** may be formed around the nanostructures **108** and on the exposed portions of the base fin structures **105**. The interfacial layers **170** may be made of silicon oxide, and the interfacial layers **170** may be formed by thermal oxidation.

(71) In some embodiments, the gate dielectric layer **172** is formed over the interfacial layer **170**, so that the nanostructures **108** are surrounded (e.g. wrapped) by the gate dielectric layer **172**. In addition, the gate dielectric layer **172** also covers the sidewalls of the spacer layers **138**, the inner spacers **142**, and the dielectric features **134** in accordance with some embodiments. The gate dielectric layers **172** may be made of one or more layers of dielectric materials, such as HfO<sub>2</sub>, HfSiO, HfSiON, HfTaO, HfTiO, HfZrO, zirconium oxide, aluminum oxide, titanium oxide, hafnium dioxide-alumina (HfO<sub>2</sub>—Al<sub>2</sub>O<sub>3</sub>) alloy, other applicable high-k dielectric materials, or a combination thereof. The gate dielectric layers **172** may be formed using CVD, ALD, other applicable methods, or a combination thereof.

(72) The first work function layer **173a** is conformally formed surrounding the nanostructures **108** in the first region **102a** and the second region **102b** in the substrate **102** (not shown). The first work function layer **173a** may be also formed over the nanostructures **108** and the dielectric features **134**. The first work function layer **173a** may be made of metal materials. The metal materials of the first work function layer **173a** may include N-work-function metal. The N-work-function metal may include tungsten (W), copper (Cu), titanium (Ti), silver (Ag), aluminum (Al), titanium aluminum alloy (TiAl), titanium aluminum nitride (TiAlN), tantalum carbide (TaC), tantalum carbon nitride (TaCN), tantalum silicon nitride (TaSiN), manganese (Mn), zirconium (Zr), or a combination thereof. The first work function layer **173a** may be formed by using CVD, ALD, other applicable methods, or a combination thereof.

(73) Next, the first work function layer **173a** in the second region **102b** of the substrate **102** is removed, as shown in FIGS. 2S, 2S-1 and 2S-2 in accordance with some embodiments. The first work function layer **173a** may be removed by a patterning process. The patterning process may include forming a patterned mask layer a photolithography process and an etching process. The photolithography process may include photoresist coating (e.g., spin-on coating), soft baking, mask aligning, exposure, post-exposure baking, developing the photoresist, rinsing and drying (e.g., hard baking). The etching process may include a wet etching process using etchant such as ammonia.

(74) Next, a second work function layer **173b** is formed surrounding the nanostructures **108** and over the nanostructures **108** in the first region **102a** and the second region **102b** in the substrate **102**, as shown in FIGS. 2S, 2S-1 and 2S-2 in accordance with some embodiments. The second work function layer **173b** may be conformally formed over the nanostructures **108** and the dielectric features **134**. The second work function layer **173b** may be made of metal materials. In some embodiments, the second work function layer **173b** includes P-work-function metal. The P-work-function metal may include titanium nitride (TiN), tungsten nitride (WN), tantalum nitride (Ta<sub>2</sub>N<sub>3</sub>), ruthenium (Ru) or a combination thereof. The second work function layer **173b** may be formed by using CVD, ALD, other applicable methods, or a combination thereof.

(75) The first work function layer **173a** and a second work function layer **173b** may be multi-layer structures. In some embodiments, the first work function layer **173a** includes the first work function layer **173a1** and the first work function layer **173a2** formed over the first work function layer **173a1**, and the second work function layer **173b** includes the second work function layer **173b1** and the second work function layer **173b2** formed over the second work function layer **173b1**.

(76) The glue layer **174** is formed over the first work function layer **173a** and the second work function layer **173b**, as shown in FIGS. 2S, 2S-1 and 2S-2 in accordance with some embodiments. The glue layers **174** may be made of one or more layers of conductive material, such as aluminum, copper, titanium, tantalum, tungsten, cobalt, molybdenum, tantalum nitride, nickel silicide, cobalt silicide, TiN, WN, TiAl, TiAlN, TaCN, TaC, TaSiN, metal alloys, another suitable material, or a

combination thereof. The glue layers **174** may be formed using CVD, ALD, electroplating, another applicable method, or a combination thereof. After the glue layer **174** is formed, a planarization process such as CMP or an etch-back process may be performed and the protection layer **164** may be exposed.

(77) After the gate structures **168** are formed, an etch back process is performed to remove the top portions of the gate structures **168** and the protection layers **164** over the ILD structure, and a recess **175** is formed over the nanostructures **108** between the gate spacers **138**, as shown in FIGS. 2T, 2T-1 and 2T-2 in accordance with some embodiments. The top portion of the dielectric material **126a** and the top surfaces of the first gate dielectric layer **172**, the first work function layer **173a**, and the second work function layer **173b** are exposed after the etching process. In some embodiments, the top surface of the glue layers **174** is lower than the top surface of the dielectric material **126a** of the dielectric structure **134**. The dielectric structure **134** may provide isolation between adjacent gate structures **168**.

(78) Next, a first metal layer **178** is conformally formed over the gate structures **168**, as shown in FIGS. 2U, 2U-1 and 2U-2 in accordance with some embodiments. In some embodiments, the first metal layer **178** is in contact with the top surfaces of the gate dielectric layer **172**, the first work function layer **173a**, the second work function layer **173b**, and the glue layers **174**. In some embodiments, the first metal layer **178** is in contact with the sidewall of the spacer layers **138a**. In some embodiments, the top surface of the first metal layer **178** is lower than the top surface of the spacer layers **138a**. In some embodiments, the first metal layer **178** is in a U-shape in a cross-sectional view. The first metal layer **178** may be deposited directly.

(79) In some embodiments, the metal layer **178** is made of high conductive metal such as Ru, TiN, TaN, Co, Ti, TiAl, W, copper, tantalum, molybdenum, nickel silicide, cobalt silicide, WN, TiAlN, TaCN, TaC, TaSiN, metal alloys, another suitable material, or the like. The metal layer **178** may be formed by using CVD, ALD, electroplating, another applicable method, or a combination thereof.

(80) In some embodiments, the thickness of the first metal layer **178** over the gate structure **168** and over the sidewalls of the spacer layers **138** are substantially the same. In some embodiments, the thickness of the first metal layer **178** is in a range of about 2 nm to about 3 nm. If the first metal layer **178** is too thick, the parasitic capacitance may be increased due to thicker first metal layer **178** in the Y direction. If the first metal layer **178** is too thin, the capacitance reduction may be not enough. The thickness of the first metal layer **178** may be controlled by the deposition time or cycle number.

(81) Next, a second metal layer **180** is formed over the first metal layer **178**, as shown in FIGS. 2V, 2V-1 and 2V-2 in accordance with some embodiments. After the second metal layer **180** is formed, an etch-back process may be performed to remove excess second metal layer material **180** and expose the top surface of the first metal layer **178**.

(82) In some embodiments, the top surface of the first metal layer **178** is substantially level with the top surface of the second metal layer **180** after the etching back process. In some embodiments, the second metal layer **180** is surrounded by the first metal layer **178**. The second metal layer **180** may be formed using CVD, ALD, electroplating, another applicable method, or a combination thereof.

(83) In some embodiments, the first metal layer **178** and the second metal layer **180** are made of different materials with different etching selectivity. In some embodiments, the second metal layer **180** is made of W.

(84) In some embodiments, the total thickness H of the first metal layer **178** and the second metal layer **180** is in a range of about 3 nm to about 8 nm. If the total thickness H of the first metal layer **178** and the second metal layer **180** is too thick, the parasitic capacitance may be too great. If the total thickness H of the first metal layer **178** and the second metal layer **180** is too thin, the capacitance reduction may be not enough, and the resistance may be increased.

(85) Next, the first metal layer **178** formed over opposite sides of the second metal layer **180** is

selectively etched and the gate electrode layer **181** is formed, as shown in FIGS. 2W, 2W-1 and 2W-2 in accordance with some embodiments. The gate electrode layer **181** may include the first metal layer **178** and the second metal layer **180**. In some embodiments, an inverted T-shape gate structure **168** with the gate electrode layer **181** is formed after the etching process. In some embodiments, the gate electrode layer **181** is narrower than the bottom surface of the gate structure **168**.

(86) In some embodiments, the top surfaces of the gate dielectric layer **172**, the first work function layer **173a**, and the second work function layer **173b** is exposed after selectively etching the first metal layer **178**. The first metal layer **178** and the second metal layer **180** may be separated from the spacer layers **138**. In some embodiments, the sidewall of the first metal layer **178** is aligned with the sidewall of the second metal layer **180**. In some embodiments, the distance D between the first metal layer **178** and the spacer layers **138** and the thickness T of the first metal layer **178** are substantially the same. The etching process may include a dry etching process or a wet etching process. In some embodiments, the etching process is a dry etching process.

(87) Next, a cap layer **182** is formed in the recess **175** above the gate structure **168**, as shown in FIGS. 2X, 2X-1 and 2X-2 in accordance with some embodiments. In some embodiments, the cap layer **182** covers the first metal layer **178** and the second metal layer **180**. In some embodiments, the cap layer **182** is formed over the top surface and of the second metal layer **180** and the sidewalls of the first metal layer **178** and the second metal layer **180**. In some embodiments, the cap layer **182** covers the top surface and the sidewalls of the gate electrode layer **181**.

(88) The cap layer **182** may be formed between the spacers **138**. In some embodiments, the cap layer **182** has an extending portion **182e** protruding between the second metal layer **180** and the spacer layer **138**. The extending portion **182e** of the cap layer **182** may be between the gate electrode layer **181** and the spacer layer **138**. In some embodiments, the cap layer **182** is in contact with the top surfaces of the gate dielectric layer **172**, the first work function layer **173a**, and the second work function layer **173b**. In some embodiments, the cap layer **182** is in contact with the sidewalls of the first metal layer **178** and the second metal layer **180**. In some embodiments, the bottom surface of the cap layer **182** is lower than the top surface of the second metal layer **180**.

(89) With the extending portion **182e** of the cap layer **182** formed between the gate electrode layer **181** and the spacer layers **138**, the parasitic capacitance between the gate structure **168** and the subsequently formed source/drain contact structure may be reduced, and the device performance may be enhanced.

(90) The cap layer **182** may provide isolation for subsequently formed contact structure and conductive elements nearby. The cap layer **182** may be made of dielectric materials such as SiN, LaO, AlO, Si, YO, TaCN, ZrSi, SiOCN, SiOC, SiCN, LaO, ZrN, ZrAlO, TiO, TaO, ZrO, HfO, SiN, HfSi, AlON, SiO, SiC, ZnO, other applicable materials, or a combination thereof. The cap layer **182** may be deposited in the recess **175** by CVD (such as HDP-CVD, PECVD, or HARP), ALD, another suitable method, and/or a combination thereof. After the cap layer **182** is deposited, a planarization process (e.g., a chemical mechanical polishing process or an etching back process) may optionally be performed to remove excess cap layer materials.

(91) Next, a gate contact structure **188** is formed through the cap layer **182** and lands on the gate structure **168**, and a source/drain contact structure **186** is formed through the ILD structure **150** and lands on the source/drain epitaxial structure **144** as shown in FIGS. 2Y, 2Y-1 and 2Y-2 in accordance with some embodiments

(92) More specifically, the gate contact structure **188** and the source/drain contact structure **186** may be formed separately. For example, a trench may be formed through the ILD structure **150** to expose the source/drain epitaxial structure **144** by performing an etching process. The source/drain epitaxial structure **144** exposed by the trench may be partially etched, so that the source/drain contact structure **186** formed afterwards may have a greater contact surface with the source/drain epitaxial structure **144**. A silicide layer **184** may be formed over the source/drain structure **144** before the source/drain contact **186** is formed.

(93) A source/drain opening is formed in the ILD structure **150**, and a silicide layer **184** may be formed over the source/drain epitaxial structure **144**, as shown in FIGS. 2Y, 2Y-1 and 2Y-2 in accordance with some embodiments. The silicide layer **184** may reduce the contact resistance between the source/drain epitaxial structure **144** and the subsequently formed source/drain contact structure over the source/drain epitaxial structure **144**. The silicide layer **184** may be made of titanium silicide (TiSi<sub>sub</sub>.2), nickel silicide (NiSi), cobalt silicide (CoSi), or other suitable low-resistance materials.

(94) The silicide layer **184** may be formed over the source/drain epitaxial structure **144** by forming a metal layer over the source/drain epitaxial structure **144** first. The metal layer may react with the source/drain epitaxial structure **144** in an annealing process and a silicide layer **184** may be produced. Afterwards, the unreacted metal layer may be removed in an etching process and the silicide layer **184** may be left.

(95) Next, a barrier layer (not shown) may be conformally formed over the bottom surface and the sidewalls of the source/drain opening. Afterwards, the barrier layer may be etched back. The barrier layer remains over the bottom surface of the source/drain opening. The barrier layer may be formed before filling the conductive material in the source/drain opening to prevent the conductive material from diffusing out. The barrier layer may also serve as an adhesive or glue layer. The material of the barrier layer may be tantalum, titanium, titanium nitride, other applicable materials, or a combination thereof. The barrier layer may be formed by depositing the barrier layer materials by a physical vapor deposition process (PVD) (e.g., evaporation or sputtering), an atomic layer deposition process (ALD), an electroplating process, other applicable processes, or a combination thereof.

(96) Afterwards, a source/drain contact structure **186** is formed into the source/drain opening over the source/drain epitaxial structure **144**, as shown in FIGS. 2Y, 2Y-1 and 2Y-2 in accordance with some embodiments. The source/drain contact structure **186** may be made of aluminum (Al), copper (Cu), tungsten (W), titanium (Ti), tantalum (Ta), titanium nitride (TiN), cobalt, tantalum nitride (Ta<sub>sub</sub>N), nickel silicide (NiSi), cobalt silicide (CoSi), copper silicide, tantalum carbide (TaC), tantalum silicide nitride (TaSiN), tantalum carbide nitride (TaCN), titanium aluminide (TiAl), titanium aluminum nitride (TiAlN), other applicable conductive materials, or a combination thereof.

(97) The source/drain contact structure **186** may be formed by a chemical vapor deposition process (CVD), a physical vapor deposition process (PVD), (e.g., evaporation or sputter), an atomic layer deposition process (ALD), a plasma enhanced CVD (PECVD), a plasma enhanced physical vapor deposition (PEPVD), an electroplating process, another suitable process, or a combination thereof to deposit the conductive materials of the source/drain contact structure **186**, and then a planarization process such as a chemical mechanical polishing (CMP) process or an etch back process is optionally performed to remove excess conductive materials. After the planarization process, the top surface of the source/drain contact structure **186** may be level with the top surfaces of the ILD structure **150** and the spacer layers **138**.

(98) Similarly, the gate contact structure **188** may be formed by forming a trench exposing the second metal layer **180** and forming a conductive material. The gate contact structure **188** and the source/drain contact structure **186** may be made of the same conductive material. The gate contact structure **188** and the source/drain contact structure **186** may be formed by the same deposition process.

(99) By forming an inverted T-shape gate structure **168**, the cap layer **182** may extend into a space between the gate structure **168** and the spacer layers **138**. Therefore, the parasitic capacitance between the gate structure **168** and the source/drain contact structure **186** may be reduced. The inverted T-shape gate structure **168** may be achieved by depositing different metal layers with different etching selectivity, which is compatible with current process.

(100) Many variations and/or modifications may be made to the embodiments of the disclosure.



FIGS. 3A-3E are cross-sectional representations of various stages of forming a semiconductor device structure **10b**, in accordance with some embodiments of the disclosure. Some processes or devices are the same as, or similar to, those described in the embodiments above, and therefore the descriptions of these processes and devices are not repeated herein. The difference from the embodiments described above is that, as shown in FIG. 3A in accordance with some embodiments, the first metal layer **178** has a curved top surface.

(101) In some embodiments, the middle portion of the first metal layer **178** is lower than the side portion of the first metal layer **178**. In some embodiments, the first metal layer **178** has a concave top surface.

(102) Next, a second metal layer **180** is formed over the first metal layer **178**, as shown in FIG. 3B in accordance with some embodiments. In some embodiments, the second metal layer **180** has a curved bottom surface and a curved top surface. In some embodiments, the second metal layer **180** has a concave top surface. In some embodiments, the second metal layer **180** is narrower than the first metal layer **178**. The side portions of the first metal layer **178** may be exposed.

(103) Next, the first metal layer **178** formed over opposite sides of the second metal layer **180** is selectively etched, as shown in FIG. 3C in accordance with some embodiments. In some embodiments, a gate electrode layer **181** with curved top surface is formed after the etching process.

(104) Afterwards, a cap layer **182** with extending portions **182e** is formed over the inverted T-shape gate structure **168**, as shown in FIG. 3D in accordance with some embodiments. The source/drain contact structure **186** is formed after forming the cap layer **182**, as shown in FIG. 3E in accordance with some embodiments. The processes for selectively etching the first metal layer **178** and forming the cap layer **182** with extending portions **182e** may be the same as, or similar to, those used to selectively etch the first metal layer **178** and form the cap layer **182** in the previous embodiments. For the purpose of brevity, the descriptions of these processes are not repeated herein.

(105) By forming an inverted T-shape gate structure **168**, the cap layer **182** may extend into a space between the gate structure **168** and the spacer layers **138**. Therefore, the parasitic capacitance between the gate structure **168** and the source/drain contact structure **186** may be reduced. The inverted T-shape gate structure **168** may be achieved by depositing different metal layers with different etching selectivity, which is compatible with current process. The first metal layer **178** and the second metal layer **180** in the gate electrode layer **181** of the inverted T-shape gate structure **168** may have curved top surfaces.

(106) Many variations and/or modifications may be made to the embodiments of the disclosure. FIGS. 4A-4B are cross-sectional representations of various stages of forming a semiconductor device structure **10c**, in accordance with some embodiments of the disclosure. Some processes or devices are the same as, or similar to, those described in the embodiments above, and therefore the descriptions of these processes and devices are not repeated herein. The difference from the embodiments described above is that, as shown in FIG. 4A in accordance with some embodiments, an air gap **190** may be formed beside the first metal layer **178** of the gate electrode layer **181** when forming the cap layer **182**.

(107) In some embodiments, the air gap **190** is formed between the cap layer **182** and the gate structure **168**. In some embodiments, the cap layer **182** may be partially filled between the second metal layer **180** and the spacer layers **138**. In some embodiments, the cap layer **182** is in contact with a portion of the sidewall of the second metal layer **180**. In some embodiments, the cap layer **182** is separated from the first work function layer **173a** and the second work function layer **173b**.

(108) The source/drain contact structure **186** is formed after forming the cap layer **182**, as shown in FIG. 4B in accordance with some embodiments. The air gap **190** formed between the first metal layer **178** and the source/drain contact structure **186** may help to further reduce parasitic capacitance since the k-value of the air is lower than the k-value of the cap layer **182**. Therefore,

partially forming the cap layer **182** between the gate electrode layer **181** of the inverted T-shaped gate structure **168** and the source/drain contact structure **186** may further decrease the parasitic capacitance.

(109) It should be noted that the size of the air gap **190** shown in FIG. **4A** is merely an example, and the air gap **190** is not limited herein. The cap layer **182** may partially cover the sidewall of the first metal layer **178**, depending on the process capability.

(110) By forming an inverted T-shape gate structure **168**, the cap layer **182** may extend into a space between the gate structure **168** and the spacer layers **138**. Therefore, the parasitic capacitance between the gate structure **168** and the source/drain contact structure **186** may be reduced. The inverted T-shape gate structure **168** may be achieved by depositing different metal layers with different etching selectivity, which is compatible with current process. Forming an air gap **190** between the gate electrode layer **181** of the inverted T-shape gate structure **168** and the source/drain contact structure **186**, the parasitic capacitance may be further reduced.

(111) Many variations and/or modifications may be made to the embodiments of the disclosure. FIGS. **5A-5D** are cross-sectional representations of various stages of forming a semiconductor device structure **10d**, in accordance with some embodiments of the disclosure. Some processes or devices are the same as, or similar to, those described in the embodiments above, and therefore the descriptions of these processes and devices are not repeated herein. The difference from the embodiments described above is that, as shown in FIG. **5A** in accordance with some embodiments, a third metal layer **192** is formed between the first metal layer **178** and the second metal layer **180**.

(112) In some embodiments as shown in FIG. **5A**, after forming the first metal layer **178** with a U-shape in the cross-sectional view, the third metal layer **192** with a U-shape in the cross-sectional view is formed over the first metal layer **178**. Later, the second metal layer **180** is formed over the third metal layer **192**. The third metal layer **192** may be surrounded by the first metal layer **178**, and the second metal layer **180** may be surrounded by the third metal layer **192**. In some embodiments, the third metal layer **192** may be separated from the spacer layers **138**.

(113) In some embodiments, the third metal layer **192**, the first metal layer **178**, and the second metal layer **180** are made of different materials with different etching selectivity. In some embodiments, the third metal layer **192** is made of metal such as Ru, TiN, TaN, Co, Ti, TiAl, W, aluminum, copper, titanium, tantalum, molybdenum, nickel silicide, cobalt silicide, WN, TiAl, TiAlN, TaCN, TaC, TaSiN, metal alloys, another suitable material, or the like. The third metal layer **192** may be formed by using CVD, ALD, electroplating, another applicable method, or a combination thereof.

(114) Afterwards, the first metal layer **178**, the second metal layer **180**, and the third metal layer **192** is etched back to remove excess materials of the first metal layer **178**, the second metal layer **180**, and the third metal layer **192**, so that the top surfaces of first metal layer **178**, the second metal layer **180**, and the third metal layer **192** are substantially at the same level, as shown in FIG. **5A** in accordance with some embodiments.

(115) Next, the first metal layer **178** formed over opposite sides of the second metal layer **180** and the third metal layer **192** is selectively etched, as shown in FIG. **5B** in accordance with some embodiments. In some embodiments, an inverted T-shape gate structure **168** with a gate electrode layer **181** is formed after the etching process. In some embodiments, the gate electrode layer **181** includes the third metal layer **192** surrounding the second metal layer **181** formed over the first metal layer **178**.

(116) After the etching process, the top surfaces of the third metal layer **192** and the second metal layer **180** may be exposed. In addition, the sidewalls of the first metal layer **178** and the third metal layer **192** may be also exposed. The inverted T-shape gate structure **168** with an extra third metal layer **192** may provide flexibility to modify the gate resistance. The source/drain contact structure **186** is formed after forming the cap layer **182**, as shown in FIG. **5D** in accordance with some embodiments.

(117) It should be noted that, the number of the metal layers **178/192/180** of the gate electrode layer **181** of the inverted T-shape gate structure **168** shown in FIG. 5D is merely an example, and the number of the metal layers of the inverted T-shape gate structure **168** is not limited herein, depending on the demands. The combination of different metal layers **178/192/180** may result in different gate resistance.

(118) By forming an inverted T-shape gate structure **168**, the cap layer **182** may extend into a space between the gate structure **168** and the spacer layers **138**. Therefore, the parasitic capacitance between the gate structure **168** and the source/drain contact structure **186** may be reduced. The inverted T-shape gate structure **168** may be achieved by depositing different metal layers with different etching selectivity, which is compatible with current process. The gate electrode layer **181** of the inverted T-shape gate structure **168** with multi-layers such as the first metal layer **178**, the second metal layer **180**, and the third metal layer **192** may provide flexibility to modify the gate resistance.

(119) Many variations and/or modifications may be made to the embodiments of the disclosure. FIGS. 6A-6C are cross-sectional representations of various stages of forming a semiconductor device structure **10e**, in accordance with some embodiments of the disclosure. Some processes or devices are the same as, or similar to, those described in the embodiments above, and therefore the descriptions of these processes and devices are not repeated herein. The difference from the embodiments described above is that, as shown in FIG. 6A in accordance with some embodiments, the first cap layer **182a** only partially fill the recess **175** between the spacer layers **138**.

(120) In some embodiments as shown in FIG. 6A, the first cap layer **182a** fills up the space between the first metal layer **178** of the gate electrode layer **181** and the spacer layers **138**. In some embodiments, the top surface of the first cap layer **182a** is lower than the top surface of the spacer layers **138**. The first cap layer **182a** may be made of dielectric materials such as LaO, AlO, Si, YO, TaCN, ZrSi, SiOCN, SiOC, SiCN, LaO, ZrN, ZrAlO, TiO, TaO, ZrO, HfO, SiN, HfSi, AlON, SiO, SiC, ZnO, other applicable materials, or a combination thereof. The first cap layer **182a** may be deposited in the recess **175** by CVD (such as HDP-CVD, PECVD, or HARP), ALD, another suitable method, and/or a combination thereof.

(121) Next, a second cap layer **182b** is formed over the first cap layer **182a** in the recess **175** between the spacer layers **138**, as shown in FIG. 6B in accordance with some embodiments. In some embodiments, the first cap layer **182a** and the second cap layer **182b** are made of different materials. The cap layer structure **182** is a multi-layer structure including the first cap layer **182a** and the second cap layer **182b**. The multi-layer cap layer structure **182** may provide flexibility to modify the parasitic capacitance. The source/drain contact structure **186** is formed after forming the cap layer **182**, as shown in FIG. 6C in accordance with some embodiments.

(122) It should be noted that, the number of the cap layers **182a** and **182b** of the shown in FIG. 6C is merely an example, and the number of the cap layers is not limited herein, depending on the demands. The combination of different cap layers **182a** and **182b** may result in different capacitance.

(123) By forming an inverted T-shape gate structure **168**, the cap layer **182** may extend into a space between the gate structure **168** and the spacer layers **138**. Therefore, the parasitic capacitance between the gate structure **168** and the source/drain contact structure **186** may be reduced. The inverted T-shape gate structure **168** may be achieved by depositing different metal layers with different etching selectivity, which is compatible with current process. The multi-layer cap layer structure **182a** and **182b** may provide flexibility to modify the parasitic capacitance.

(124) As described previously, an inverted T-shape gate structure **168** is formed by forming gate electrode layer **181** with different metal layers with etching selectivity. The cap layer **182** may be formed between the inverted T-shape gate structure **168** and the source/drain contact structures **186**. Therefore, the parasitic capacitance may be reduced and the device performance may be enhanced. In some embodiments as shown in FIG. 3E, the gate electrode layer **181** of the inverted T-shape

gate structure **168** have curved top surfaces. In some embodiments as shown in FIG. 4B, an air gap **190** is formed between the inverted T-shape gate structure **168** and the source/drain contact structures **186**. The parasitic capacitance is further reduced with the air gap **190**. In some embodiments as shown in FIG. 5D, multiple metal layers **178**, **180**, and **192** are formed in the gate electrode layer **181** of the inverted T-shape gate structure **168**. With more metal layers formed in the gate electrode layer **181** of the inverted T-shape gate structure **168**, there is more flexibility to modify the gate resistance. In some embodiments as shown in FIG. 6C, multiple cap layers **182a** and **182b** cover the inverted T-shape gate structure **168**. With multiple cap layers **182a** and **182b** formed over the inverted T-shape gate structure **168**, there is more flexibility to modify the parasitic capacitance.

(125) Embodiments of a semiconductor device structure and a method for forming the same are provided. By depositing metal layers with different etching selectivity, an inverted T-shape gate structure is formed after a selective etching process. The cap layer may extend in the space between the inverted T-shape gate structure and the source/drain contact structure. The parasitic capacitance may be reduced and the device performance may be enhanced.

(126) In some embodiments, a method for forming a semiconductor device structure is provided. The method for forming a semiconductor device structure includes forming nanostructures over a substrate. The method for forming a semiconductor device structure also includes forming a work function layer surrounding the nanostructures. The method for forming a semiconductor device structure also includes forming spacers over opposite sides of the work function layer. The method for forming a semiconductor device structure also includes forming a first metal layer over the work function layer and sidewalls of the spacers. The method for forming a semiconductor device structure also includes forming a second metal layer surrounded by the first metal layer. The method for forming a semiconductor device structure also includes etching the first metal layer over opposite sides of the second metal layer. The method for forming a semiconductor device structure also includes forming a cap layer over the top surface and sidewall of the second metal layer.

(127) In some embodiments, a method for forming a semiconductor device structure is provided. The method for forming a semiconductor device structure includes forming a fin structure with alternating stacked first semiconductor layers and second semiconductor layers over a substrate. The method for forming a semiconductor device structure also includes removing the first semiconductor layers to form a gate opening between the second semiconductor layers. The method for forming a semiconductor device structure also includes depositing a work function layer in the gate opening surrounding the second semiconductor layers. The method for forming a semiconductor device structure also includes forming a first metal layer with a recess over the work function layer. The method for forming a semiconductor device structure also includes forming a second metal layer in the recess. The method for forming a semiconductor device structure also includes removing the first metal layer over opposite sides of the second metal layer. The method for forming a semiconductor device structure also includes forming a cap layer covering the first metal layer and the second metal layer.

(128) In some embodiments, a semiconductor device structure is provided. The semiconductor device structure includes nanostructures formed over a substrate. The semiconductor device structure also includes a gate structure surrounding the nanostructures. The semiconductor device structure also includes spacers formed over opposite sides of the gate structure over the nanostructures. The semiconductor device structure also includes a first metal layer formed over the gate structure. The semiconductor device structure also includes a second metal layer formed over the first metal layer. The semiconductor device structure also includes a first cap layer formed over the second metal layer. The first cap layer has an extending portion between the second metal layer and the spacers.

(129) The foregoing outlines features of several embodiments so that those skilled in the art may

better understand the aspects of the present disclosure. Those skilled in the art should appreciate that they may readily use the present disclosure as a basis for designing or modifying other processes and structures for carrying out the same purposes and/or achieving the same advantages of the embodiments introduced herein. Those skilled in the art should also realize that such equivalent constructions do not depart from the spirit and scope of the present disclosure, and that they may make various changes, substitutions, and alterations herein without departing from the spirit and scope of the present disclosure.

## Claims

1. A method for forming a semiconductor device structure, comprising: forming nanostructures over a substrate; forming spacers over the nanostructures; forming a work function layer surrounding the nanostructures; forming a first metal layer over the work function layer and sidewalls of the spacers; forming a second metal layer surrounded by the first metal layer; etching the first metal layer over opposite sides of the second metal layer; and forming a cap layer over a top surface and a sidewall of the second metal layer, wherein a bottom surface of the cap layer is lower a bottom surface of the second metal layer.
2. The method for forming the semiconductor device structure as claimed in claim 1, wherein the first metal layer has a different etching selectivity than the second metal layer.
3. The method for forming the semiconductor device structure as claimed in claim 1, wherein a top surface of the work function layer is exposed after etching the first metal layer.
4. The method for forming the semiconductor device structure as claimed in claim 1, wherein the cap layer is in contact with a top surface of the work function layer.
5. The method for forming the semiconductor device structure as claimed in claim 1, wherein the top surface of the cap layer is lower than a top surface of the spacers.
6. The method for forming the semiconductor device structure as claimed in claim 5, further comprising: forming a second cap layer over the first-cap layer, wherein the cap layer and the second cap layer are made of different materials.
7. The method for forming the semiconductor device structure as claimed in claim 1, wherein the cap layer covers a top surface of the spacers.
8. The method for forming the semiconductor device structure as claimed in claim 1, wherein the cap layer is in contact with an interface between the first metal layer and the second metal layer.
9. The method for forming the semiconductor device structure as claimed in claim 1, wherein the bottom surface of the cap layer is lower than an interface between the first metal layer and the second metal layer.
10. A method for forming a semiconductor device structure, comprising: forming a fin structure with alternating stacked first semiconductor layers and second semiconductor layers over a substrate; removing the first semiconductor layers to form a gate opening between the second semiconductor layers; depositing a work function layer in the gate opening surrounding the second semiconductor layers; forming a first metal layer with a recess over the work function layer; forming a second metal layer in the recess; removing the first metal layer over opposite sides of the second metal layer; and forming a cap layer covering the first metal layer and the second metal layer, wherein a bottom surface of the cap layer is lower than top surface of the first metal layer.
11. The method for forming the semiconductor device structure as claimed in claim 10, further comprising: forming a third metal layer in the recess; wherein the second metal layer is surrounded by the third metal layer.
12. The method for forming the semiconductor device structure as claimed in claim 11, further comprising: etching back the first metal layer, the second metal layer, and the third metal layer.
13. The method for forming the semiconductor device structure as claimed in claim 10, wherein the cap layer is in contact with a portion of the sidewall of the second metal layer.

14. A method for forming a semiconductor device structure, comprising: forming nanostructures over a substrate; forming spacers over the nanostructures; forming a work function layer between the spacers; depositing a first metal layer over the work function layer; depositing a second metal layer over the first metal layer; and forming a cap layer covering the second metal layer and having an extending portion between the second metal layer and the spacers, wherein the cap layer has a first bottom surface in contact with the work function layer and a second bottom surface in contact with the second metal layer, and the first bottom surface is lower than the second bottom surface.
15. The method for forming the semiconductor device structure as claimed in claim 14, further comprising: partially removing the first metal layer so that a sidewall of the first metal layer is substantially aligned with a sidewall of the second metal layer.
16. The method for forming the semiconductor device structure as claimed in claim 14, wherein the first metal layer and the second metal layer have curved top surfaces.
17. The method for forming the semiconductor device structure as claimed in claim 14, further comprising: forming an air gap formed between the extending portion of the cap layer and the work function layer.
18. The method for forming the semiconductor device structure as claimed in claim 14, further comprising: forming a third metal layer after forming the first metal layer and before forming the second metal layer; and partially removing the first metal layer so that a sidewall of the first metal layer is substantially aligned with a sidewall of the second metal layer and substantially aligned with a sidewall of the third metal layer.
19. The method for forming the semiconductor device structure as claimed in claim 18, wherein the third metal layer is separated from the spacers by the extending portion of the cap layer.
20. The method for forming the semiconductor device structure as claimed in claim 14, further comprising: forming a second cap layer over the cap layer and covering the spacers.
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